

Semiconductor	SiC
Polytype	4H
Diameter	150 mm



Table 1. SUBSTRATE Specifications

Parameter	Specification	Unit	Test Method
Poly-Type	4H-N-type		
Crystal Orientation	4.0° towards $\langle 11\bar{2}0 \rangle \pm 0.5^\circ$		
Dopant	Nitrogen		
Dopant Type	N-type		
Polarity of Faces	Optical polish: Carbon face CMP: Si face ready for EPI		
Nominal Diameter	150±0.25	mm	
Resistivity	0.02±0.005	Ωcm	
Primary Flat Length	47.5±2.5	mm	
Primary Flat Location	with flat parallel to $\langle 11\bar{2}0 \rangle$ direction±5°	deg	
Thickness	350±25	μm	
Total Thickness Variation (TTV)	≤10	μm	
Warp	≤40	μm	
Bow	±25	μm	
Local Thickness Variation (LTV)	≤3.5	μm	10mmx10mm site size, by FRT
TUA (Total Usable Area) Based on a 3X3mm Die Grid	≥92.0	%	3mmx3mm Die Grid By Candela
Micropipe Density (MPD)	≤0.5	cm ⁻²	By Candela
BPD(Basal Plane Dislocation)	≤5000	cm ⁻²	KOH etching
TSD(Threading Screw Dislocation)	≤300	cm ⁻²	KOH etching
Scratch Length	≤150	mm	Cumulative length per wafer By Candela
Foreign Poly Types	0	%	0 within the Fixed Quality Area,
Stains	≤2*2	cm ²	Backside stain inspection by bright light
Edge Chips	None greater than 0.5 mm width or depth.	Boolean	Inspection performed using unaided eye under bright light.
Surface Roughness	Less than 1nm within the FQA	nm	area 5 um x 5 um By AFM
Surface Metal Contamination	5E11	Atoms /cm ²	Na,K,Ca,Fe,Ni,Cu,Zn,Au,Ag,Al,Ga,Hg,As,Pt

Important Notices – Read Carefully

Before you use our products, you are requested to carefully read this document and fully understand its contents. Hunan Sanan Semiconductor Co., Ltd. (Hunan Sanan) shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of Hunan Sanan's products.

Hunan Sanan Semiconductor Datasheets are subject to change. Information presented in this document is from the characterization of engineering lots. Hunan Sanan reserves the right to change limits, test conditions, and dimensions without notice. Information contained in this document are typical values and shall in no event be regarded as a guarantee of characteristics. With respect to any information regarding the application of the product, Hunan Sanan hereby disclaims all warranties and liabilities of any kind. The information in this document is exclusively for trained technical staff. It is the responsibility of the customer's technical department to decide the suitability of the product in the customer's application and Hunan Sanan assumes no responsibility or liability whatsoever for the use of the information contained in this document.

In case there is any clause in this document or in any other documents which is contradictory to this clause, this clause shall prevail. This clause shall survive after termination of this document.

Warning

Due to technical requirements, Hunan Sanan products may contain dangerous substances. For detailed information about the substance(s), please contact the Hunan Sanan office. Hunan Sanan bears no responsibility for any damage whatsoever due to the substance(s) used in Hunan Sanan products.

Contact info

Website: <https://www.sanan-semiconductor.com/>
<https://www.sanan-semiconductor.com/en>